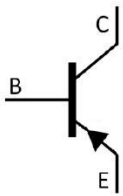


Silicon PNP transistor in a TO-220 Plastic Package.

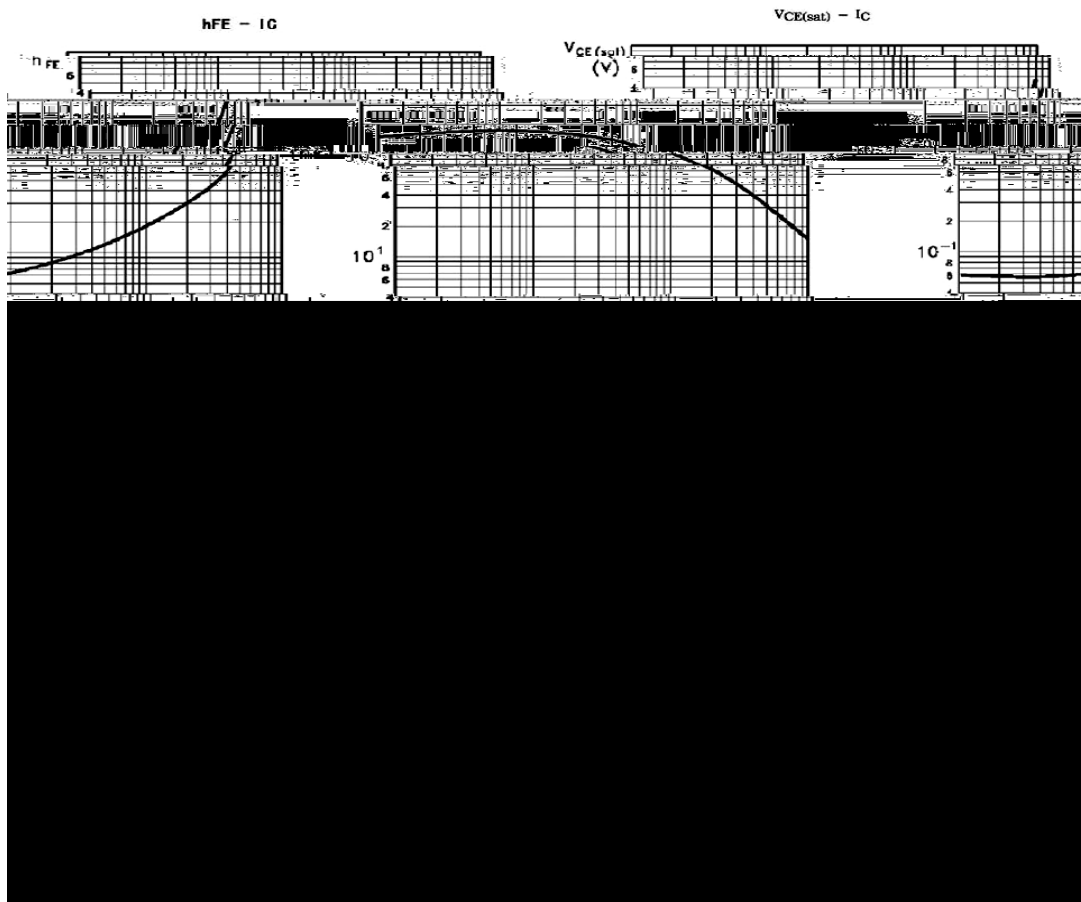
High V_{CEO} , high I_C , complement to BD911.

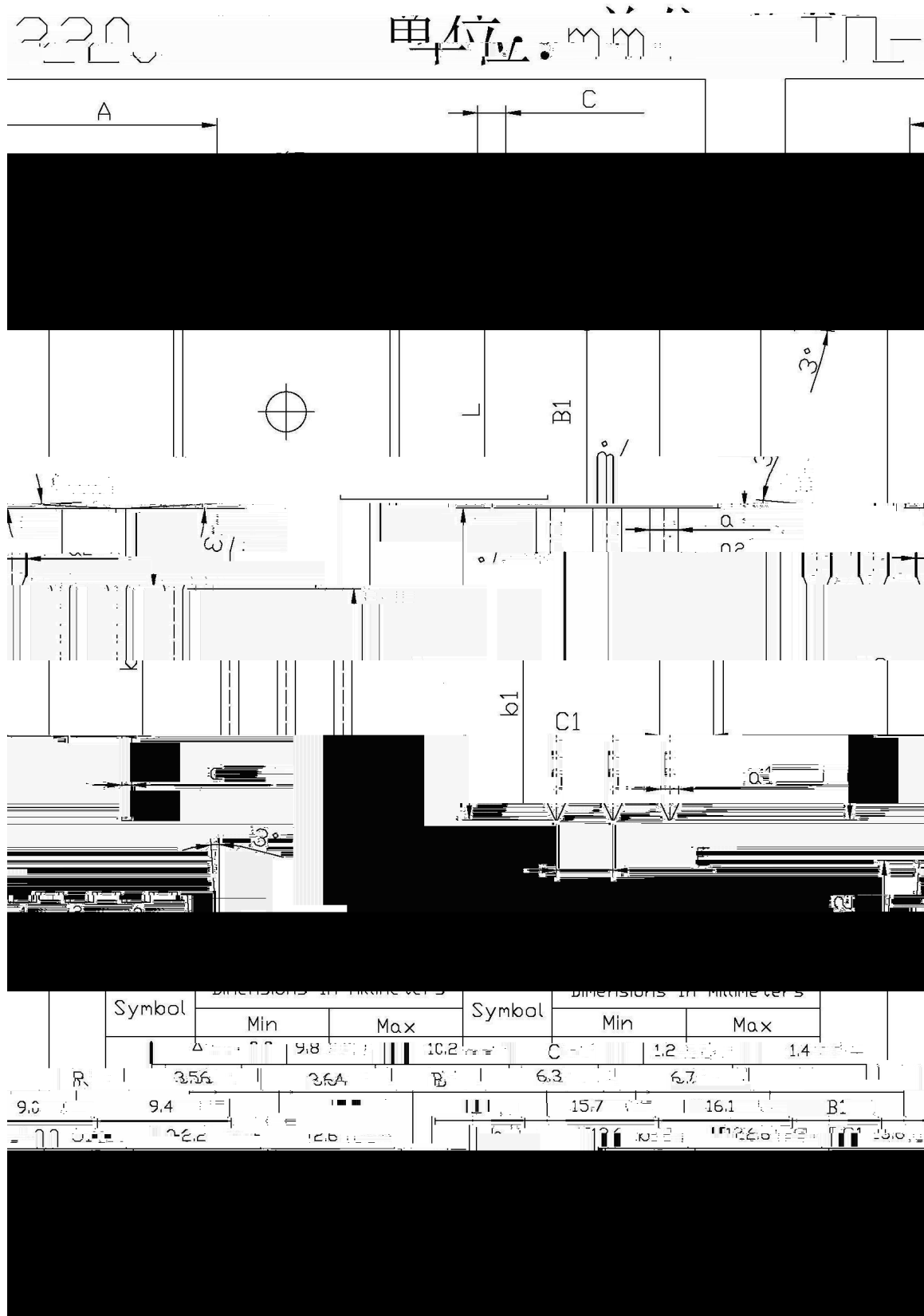
Use in power linear and switching applications.

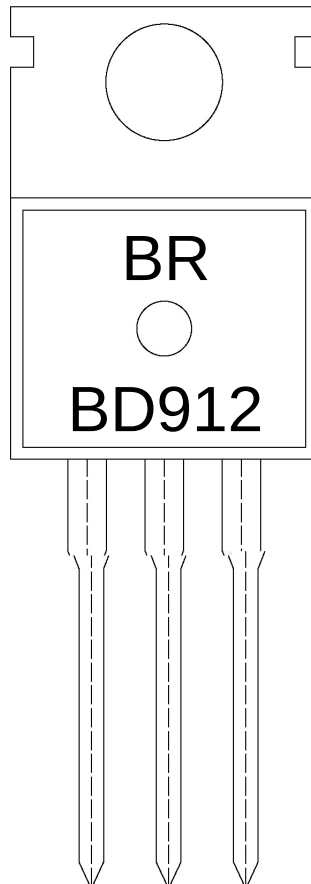


PIN1	Base	PIN 2	Collector	PIN 3	Emitter
Hi	ref57.66	259./lm 0 66	ref62.94	831.2403	Tm θ_{JA} 4757.66 260506D912 6

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-15	A
Base Current – Continuous	I_B	-5.0	A
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	90	W
Junction Temperature	T_j	150	





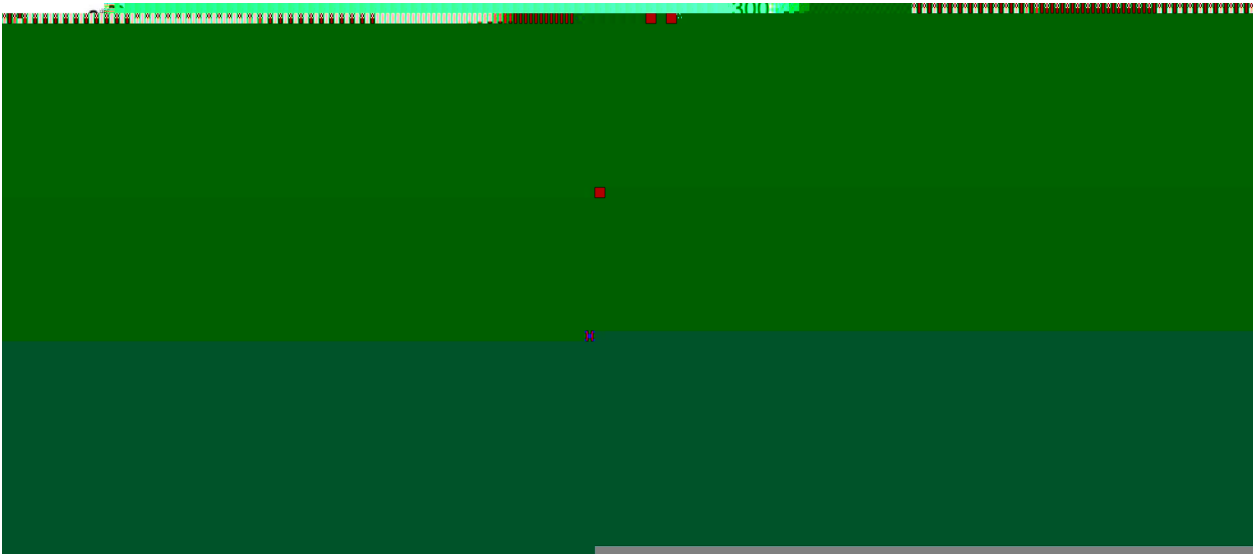


Note:

BR: Company Code

BD912: Product Type.

***: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255 5 , Duration:5 0.5sec.

3. Cooling Speed: 2~10 /sec.

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只袋	袋盒	只盒	盒箱	只箱	袋	盒	箱